

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated circuit device has: a layer insulating film formed on a semiconductor substrate; a fuse portion which is configured by an uppermost metal wiring layer that is formed on the layer insulating film; an inorganic insulating protective film which is formed on the metal wiring layer and the layer insulating film; and an organic insulating protective film which is formed on the inorganic insulating protective film. An opening is formed in the organic insulating protective film so that the inorganic insulating protective on the fuse portion is exposed. According to this configuration, it is not required to etch away the layer insulating film in order to form an opening above the fuse portion. Therefore, the time period required for forming the opening can be shortened and the whole production time period can be shortened. Since only the inorganic insulating protective film is formed above the fuse portion, the cutting off of the fuse portion can be performed without excessively increasing the irradiation energy of a laser beam. Therefore, high reliability and high productivity can be realized without causing the lowering of the reliability and the reduction of the production yield which are due to the cutting off of the fuse portion. Since the fuse portion is covered with the inorganic insulating protective film, the moisture resistance can be improved.